

## **Advanced materials processing with intelligent systems**

### **Light materials interaction**

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# Content

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- Light meets materials
  - Reflection
  - Transmission
  - Scattering
  - Absorption
- Time scales of effects
  - Fluorescence
  - Heating

# Light absorption

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- Light that is absorbed makes a photon disappear !
  - Where is the energy going?
- Time scales of effects
  - Fluorescence
  - Heating

# Absorption & Fluorescence

Absorption & fluorescence  
in a single molecule, ion,  
atom

!

non-radiative transition  
→ transformation into  
heat

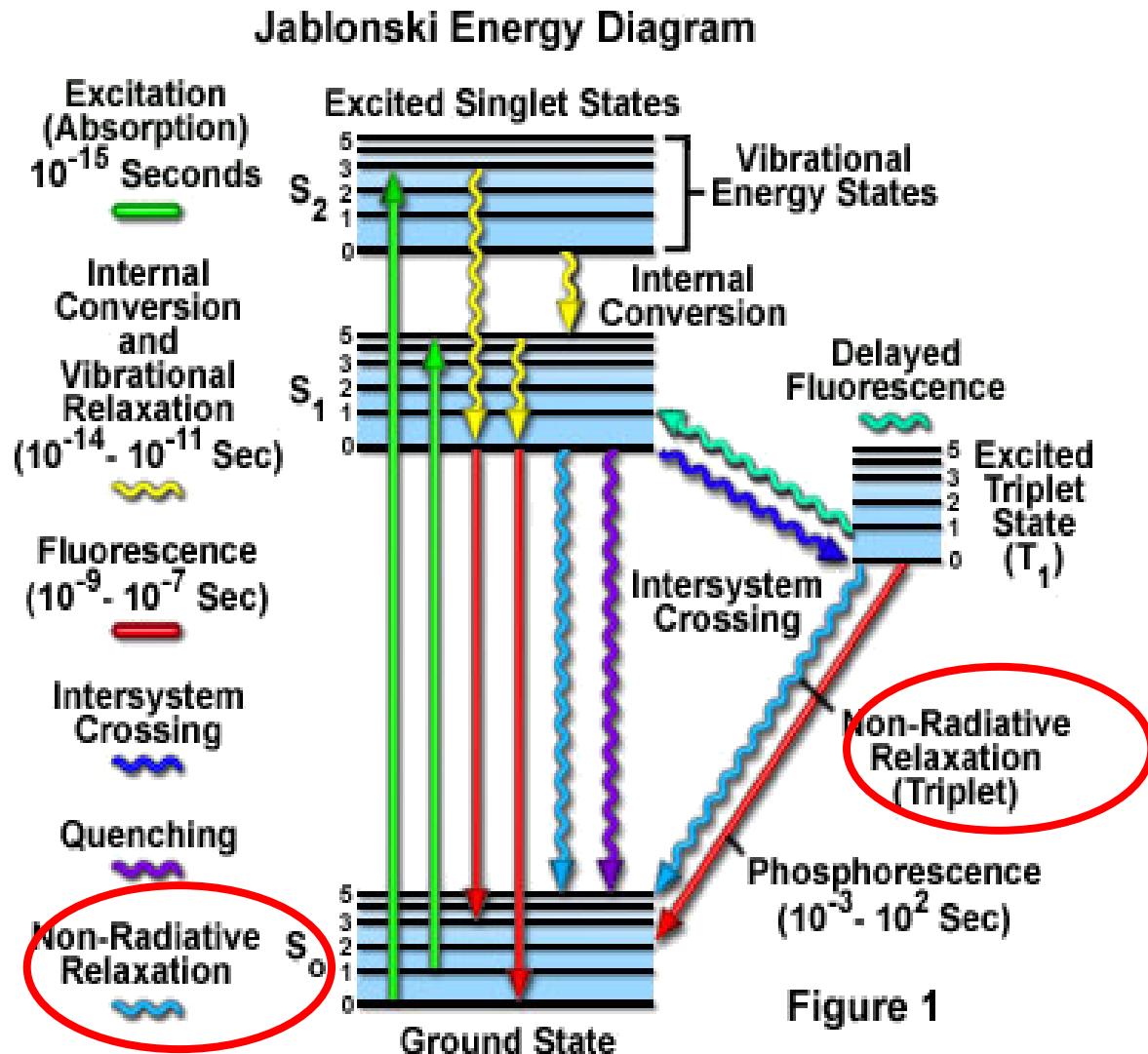


Figure 1

<http://micro.magnet.fsu.edu/primer/techniques/fluorescence/fluorescenceintro.html>

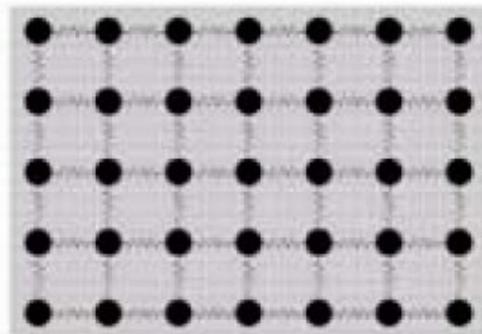
# Contents

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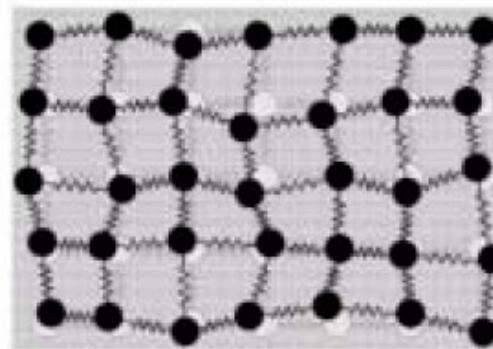
- Absorbed light → Heat
- Heat flow (heat equation)

# Heat

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$T = 0\text{K}$

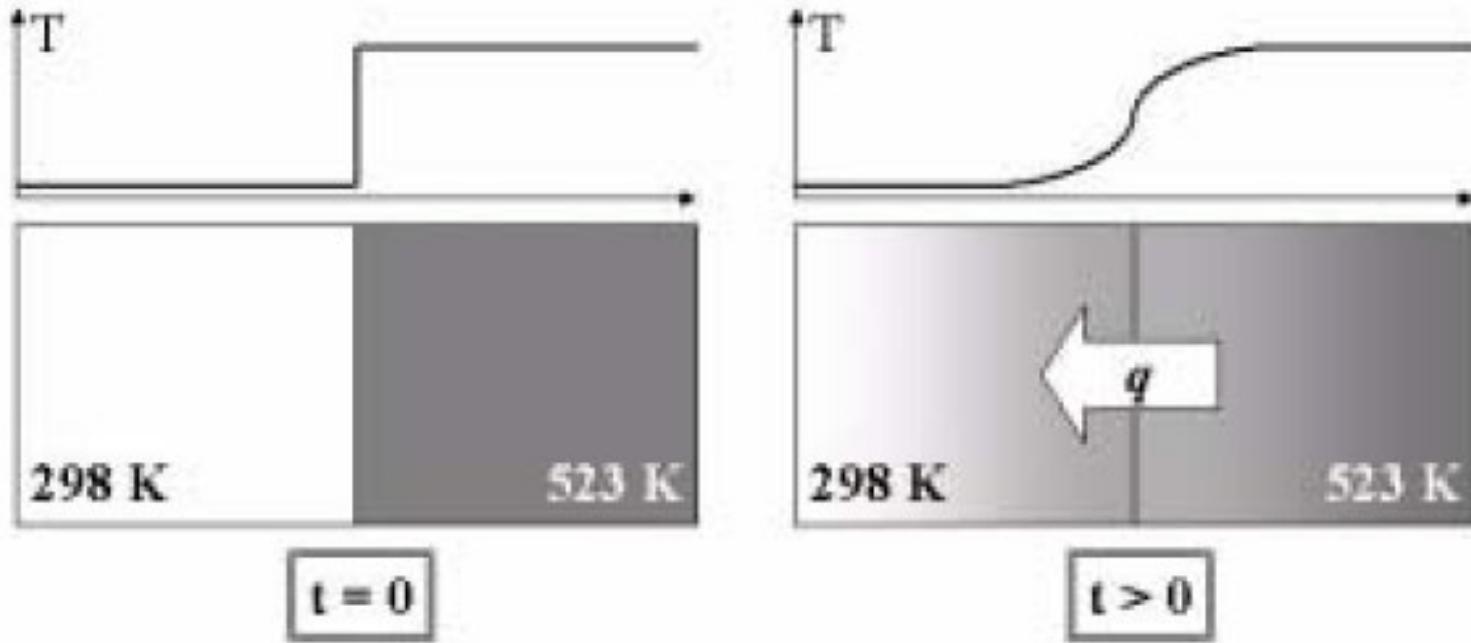


$0 < T \leq T_M$

Heat flows from warm to cold, Fourier law

Heat = energy contained in excited phonons (lattice vibrations)  
for liquids: additionally in rotation of molecules

# Heat flux



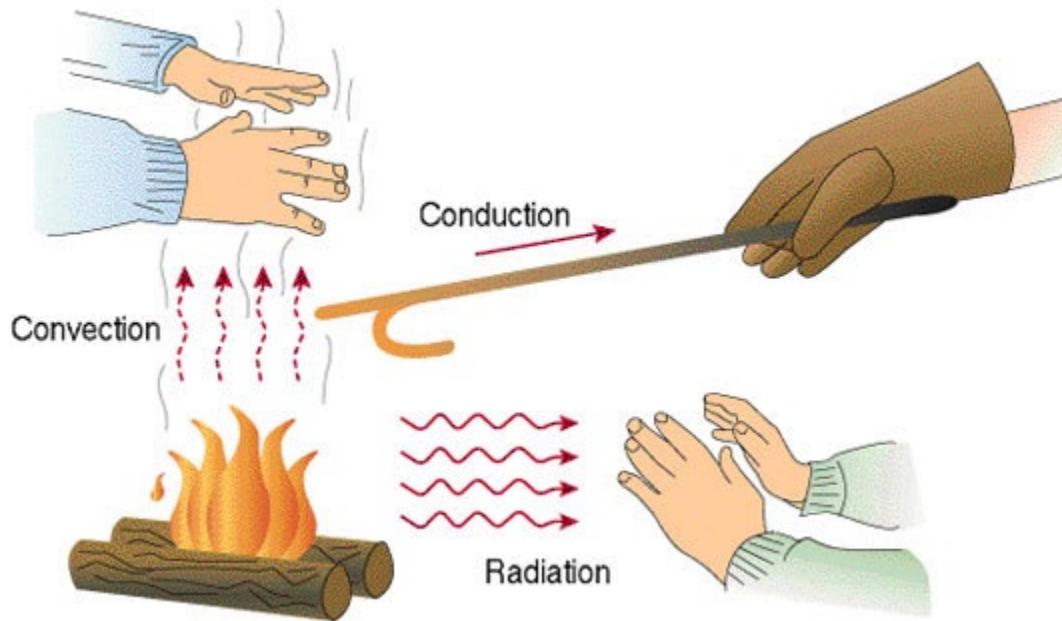
Which parameters determine the final state (temperature distribution) ?

thermal capacity, density/mass

Which parameters influence the dynamics of the flow?

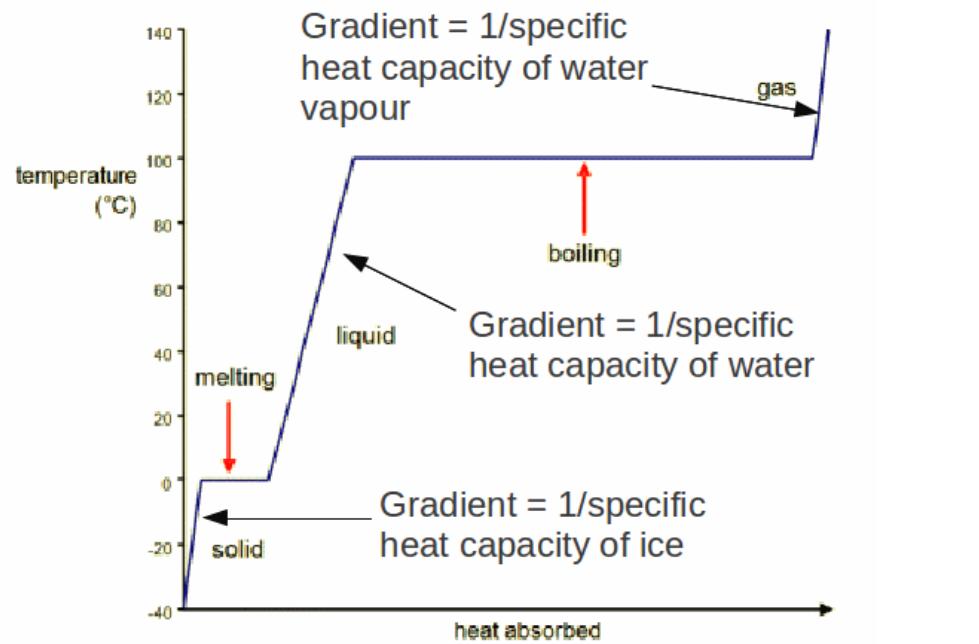
thermal capacity, thermal conductivity, density

# How heat can be transported?

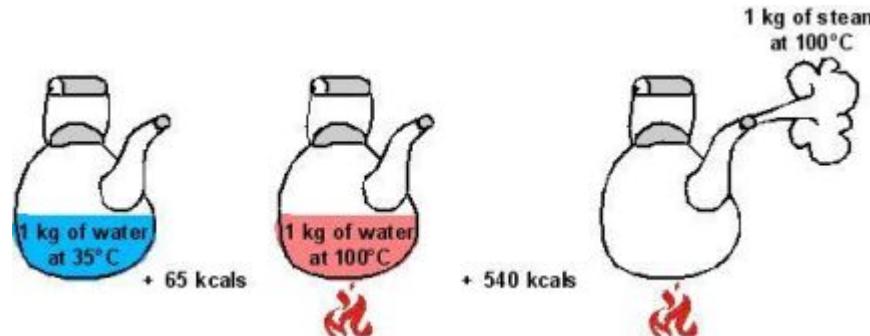


Other (indirect) means?

# Phase Transition



evaporation needs  
much more (5x-10x)  
energy than melting  
and heating the  
material !!!



# Transport Phenomena

- Heat flow
- Materials flow (diffusion)
- Viscosity

Driving force for transport are spatial inhomogeneities, i.e. gradients

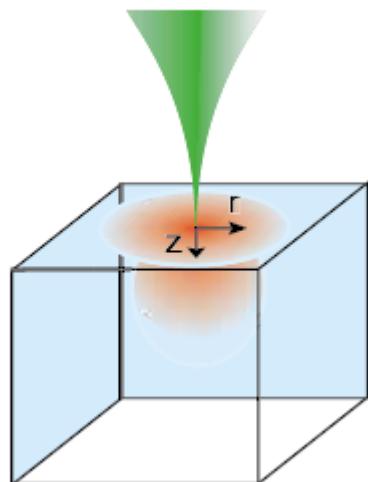
$$\mathbf{j} = -C \mathbf{grad} \phi$$

$$\frac{\partial \phi}{\partial t} = C \nabla^2 \phi$$

Transported quantity	System state	Material property
Nom de l'éq. V.1-1	$\mathbf{j}$	$\phi$
Fourier	Heat flow	$T$
Fick	Mass flow	$[n]$
Newton	Momentum flow	$\mathbf{v}$

# Heat flow

form of the equation in case the external heat source is present



how temperature field  
changes in time

$$\frac{\partial T}{\partial t} = D \nabla^2 T + \frac{Q}{\rho c_p} \delta(\vec{x}, t)$$

based on existing  
temperature  
distribution

and external heat  
sources and heat  
losses

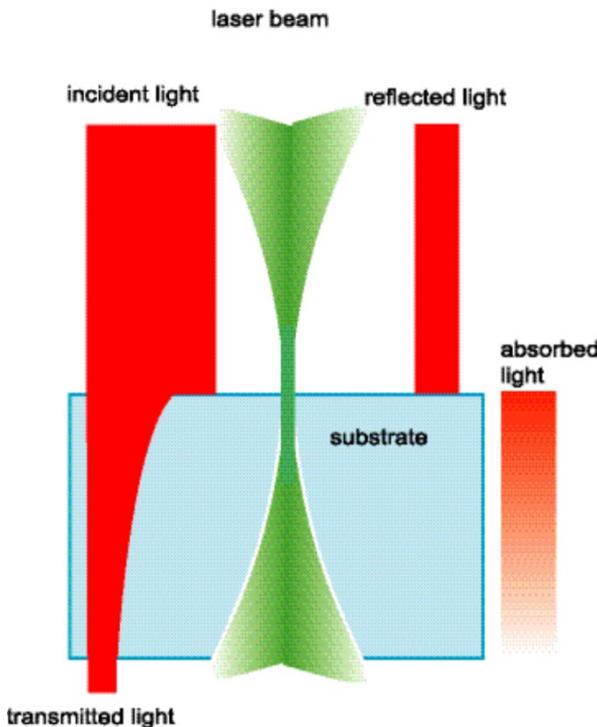
# Heat Source – Laser Irradiation

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- Heat flux
  - Laser heating depends on a large number of parameters
    - Optical properties of material ( $R, \alpha, \dots$ )
    - Heat transport in and out of irradiation zone
    - Heat storage in and out of zone
    - Phase transition Enthalpies
    - Chemical reaction Enthalpies
    - ...

# Laser (light) Source Term

$$Q_{(x_\alpha, t)} = I_{(x, y, t)} (1 - R) f_{(z)} = I_{(a)} g_{(x, y)} f_{(z)} q_{(t)}$$



$$I_{(a)} = I_{(0)} (1 - R)$$

the (maximum) laser light intensity not reflected from surface ( $z=0$ ).

$g_{(x, y)}$  the intensity distribution of the laser light in the  $xy$ -plane.

heat distribution in depth

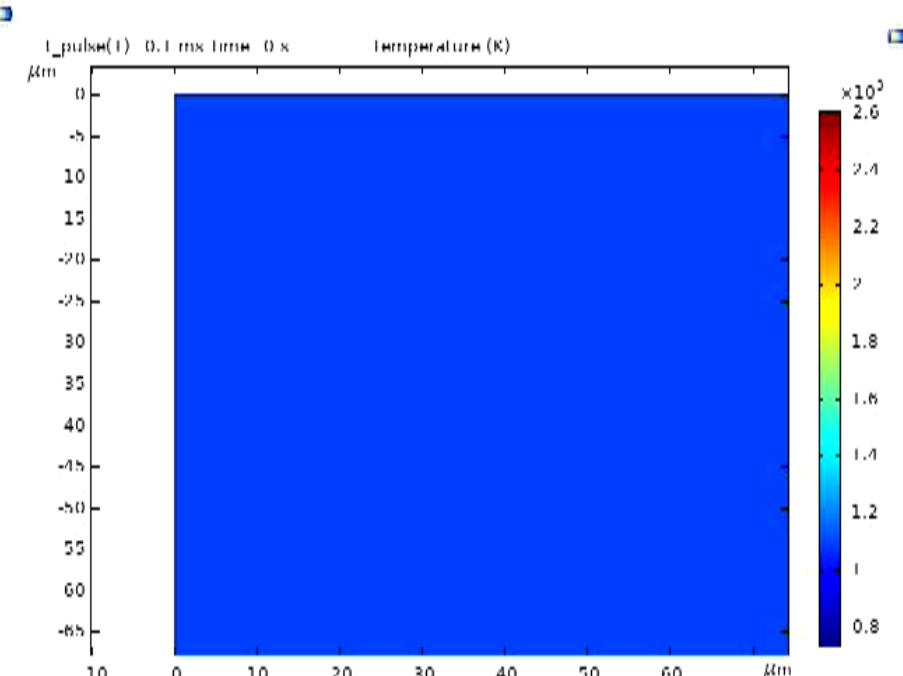
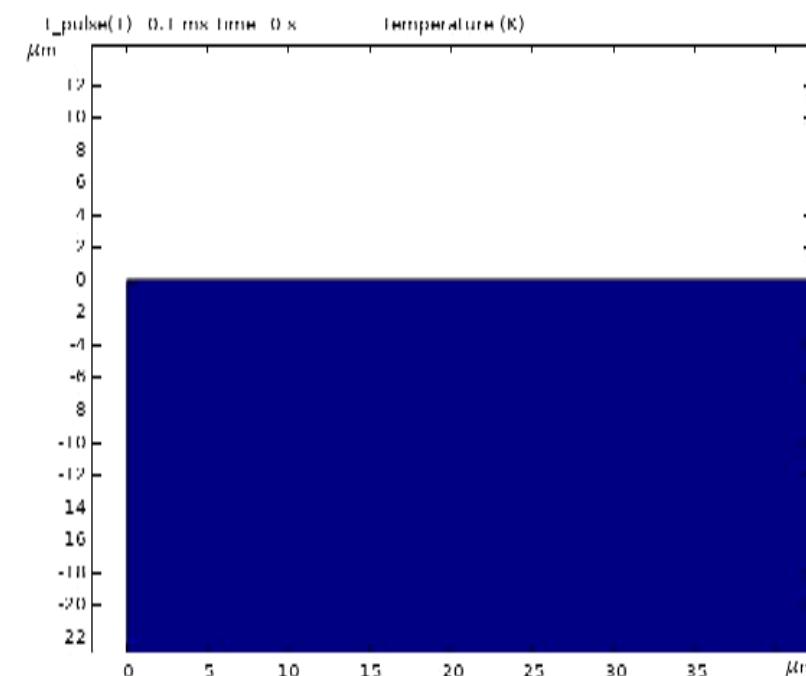
$$f_{(z)} = \alpha(T(z)) \exp \left[ - \int_0^t \alpha(T(z')) dz' \right]$$

in simplified case  $\alpha(T) = \text{const}$

$$f_{(z)} = \alpha \exp(-\alpha z)$$

# Anurag Singhania Master thesis 2020

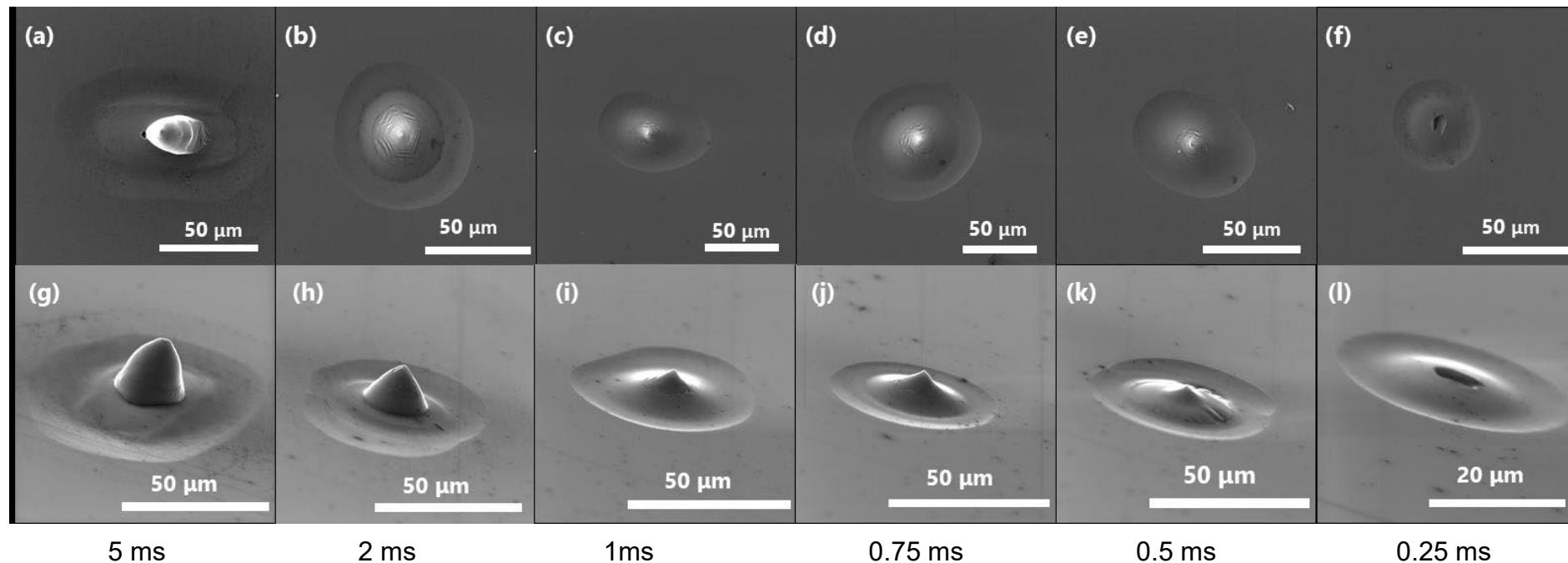
## Computational result: approach 1



# Anurag Singhania Master thesis 2020

## Experimental results

- 10 W, substrate preheated to 820 C, varying pulse durations

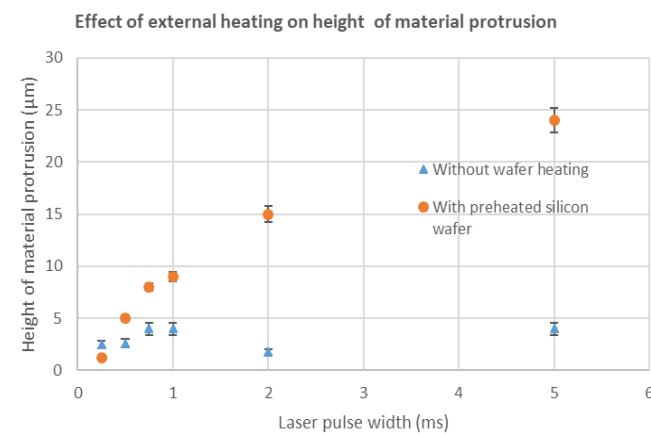
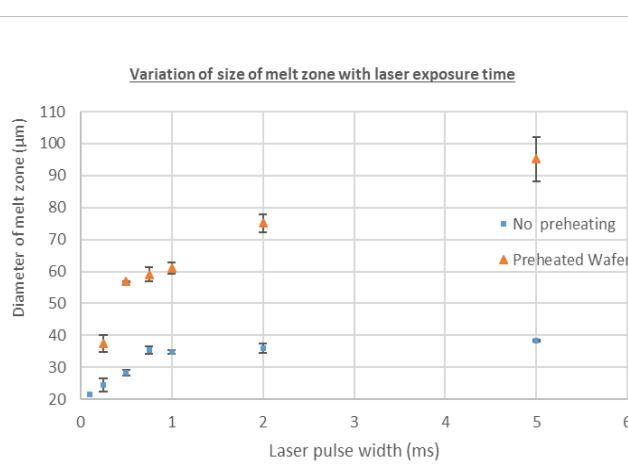


# Anurag Singhania Master thesis 2020

## Experimental results

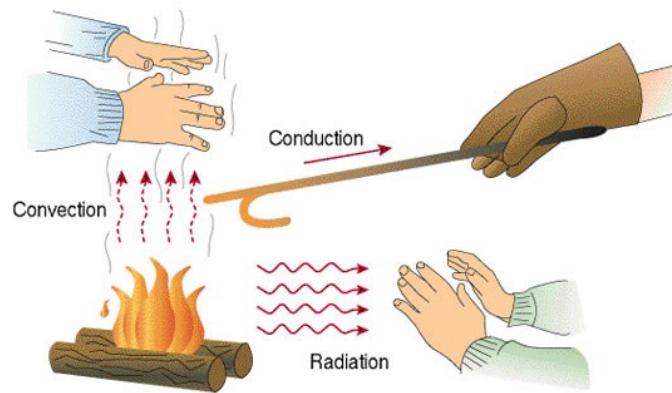
### Effect of preheating wafer

- Diameter of the melt zone increases roughly 2 to 3 times irrespective of the pulse duration
- Height of material expulsion in the center increases significantly with increase in the pulse duration



# Heat Losses and Other Terms

Conduction



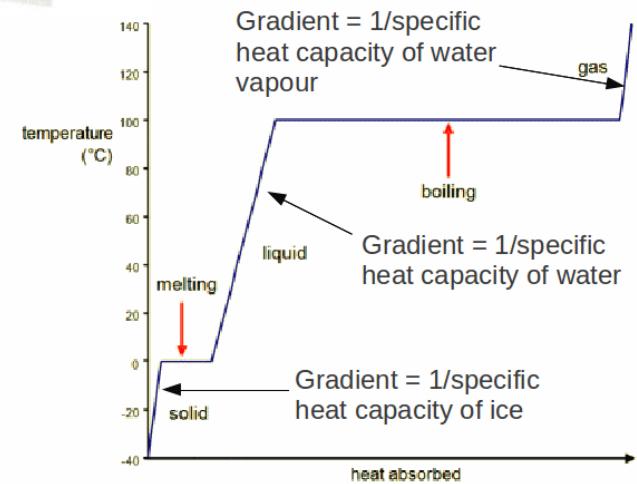
Convection

Radiation

Phase transitions



Chemical reactions



# Free Convection

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$$\eta = \eta(T)$$

$$\eta(T_s) = \eta_0 \cdot \left( \frac{T_s - T_m(\infty)}{T_m(\infty)} \right)^{\frac{1}{4}}$$

For surface  $A > 1\text{cm}^2$

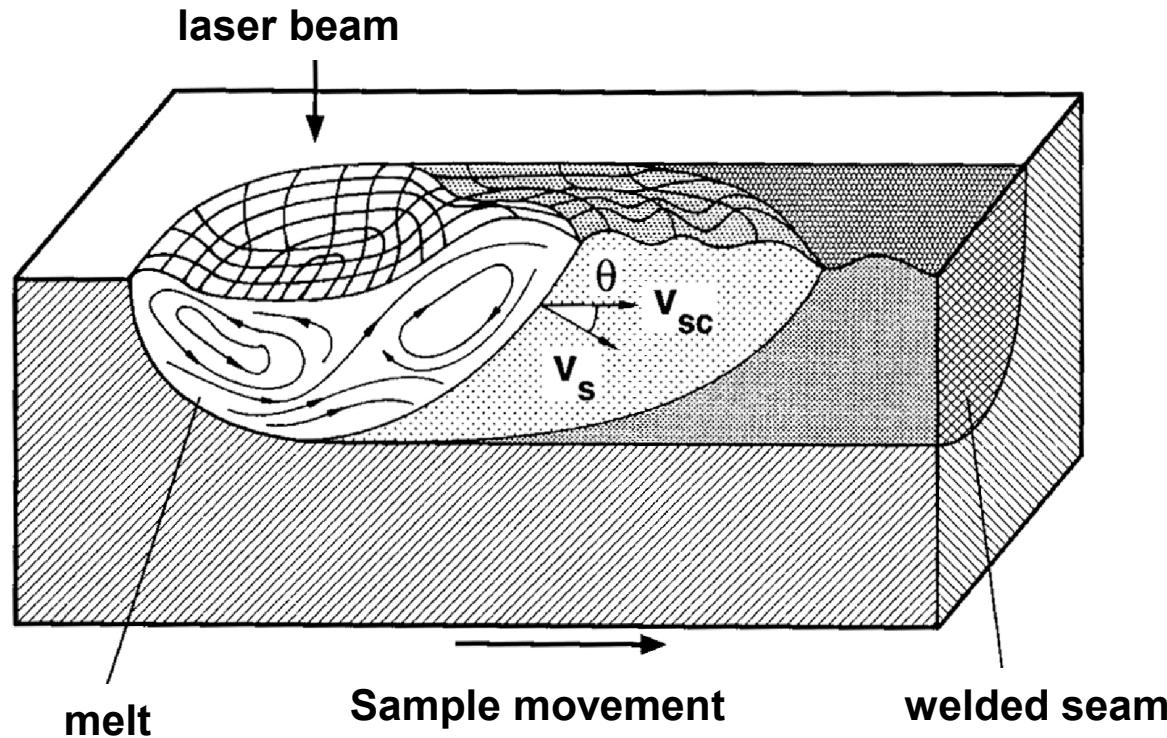
$$\text{air} \quad \eta_0 \approx 10^{-4} \left[ W / \text{cm}^2 \text{K} \right]$$

$$\text{liquid} \quad \eta_0 \approx 0.1 - 0.3 \left[ W / \text{cm}^2 \text{K} \right]$$

**cooling by gas convection is not very efficient**

# Laser Welding

Liquid convection still plays an important role in “slow” processes.  
e.g. welding (drilling, cutting)



# Radiation Cooling

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Stefan–Boltzmann law

$$J_{\text{radiat.}} = \sigma \cdot \varepsilon \cdot T^4$$

Stefan-Boltzmann constant:  $\sigma = 5.7 \cdot 10^{-12} \left[ \frac{W}{cm^2 K^4} \right]$

Total emissivity:  $\varepsilon \equiv \varepsilon(T)$

polished metal:  $\varepsilon \approx 0.02 - 0.05$

oxidized metal:  $\varepsilon \approx 0.6 - 0.7$

glass, silica:  $\varepsilon \approx 0.93$

soot:  $\varepsilon \approx 0.98$

increases very strongly  
with temperature!!!

maybe important in some  
cases.

# Phase changes & Chemical reactions

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$$Q_{phase.trans.} = v_{solid-liquid} \cdot \Delta H_{melting} + v_{liquid-gas} \Delta H_{vaporisation}$$

$$\Delta H_m = 2-10 \text{ kcal/mol} \quad \Delta H_v = 50-100 \text{ kcal/mol}$$

# Comparison: Convection - Radiation

$$J_{loss} = J_c + J_r$$

$$J_{loss} = \eta [T_s(x, y, 0, t) - T_m(\infty)] + \sigma_r \epsilon_t [T_s^4(x, y, 0, t) - T_m^4(\infty)]$$

Example:

emissivity 0.4



$$J_c \approx J_r \simeq 3 [W/cm^2]$$

$$\text{At : } T_s = 1000K$$

# Thermal Penetration Depth

- Pulsed laser irradiation results in a temperature rise in the material to a limited depth.

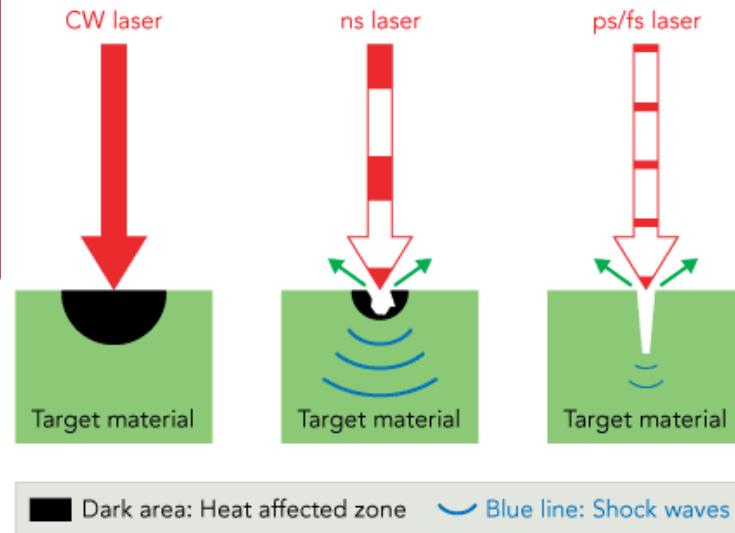
Thermal penetration depth

$$l_{thermal} = 2\sqrt{D\tau_{pulse}}$$

Heat diffusivity

$$D = \frac{\kappa}{\rho C_p}$$

$\kappa$  – heat conductivity  
 $\rho$  – material density  
 $C_p$  – heat capacity



# Table of material properties

Matériaux	$\rho$ [g/cm <sup>3</sup> ]	$T_m$ [K]	$T_v$ [K]	$c_p$ [J/gK]	$\kappa$ [W/cm K]	$D$ [cm <sup>2</sup> /s]
Al	2,7	933	2720	0,90	2,4	1,03
Al <sub>2</sub> O <sub>3</sub>	4,0	2324		0,75	0,30	
Al <sub>2</sub> O <sub>3</sub> (ceramique)	3,89	2340	3800	0,9	0,3	0,086
Au	19,3	1338	2980	0,13	3,15	1,22
C graphite	2,24	3923	4623	0,71	20; (22,3   ; 0,11 $\perp$ )	
C diamond	3,52	> 3822		0,50	20	
Cr	7,2	2130	2945	0,46	0,95	0,29
Cu	8,95	1357	2840	0,39	3,95	1,14
Fe (coulé)	7,4			0,57	0,56	0,12
Acier (0,1% C)	7,85			0,49	0,46	0,12
Acier inox (304)	8,03	1723	3273	0,5	0,15	
H <sub>2</sub> O	1	273	373	4,18	0,06	0,014

good metal

ceramics

good metal

“bad” metal

“bad” metal

water & polymer

# Cooling/heating terms

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- Convection may play a role for cooling of the whole machined piece of material – not relevant for machining
- Radiation may have contribution at very high temperatures
- In most cases cooling of the laser machined region takes place by heat conduction in the piece

# Heat equation moving substrate

heating of the material

heat brought by moving

heat conducted away

$$Q(\vec{x}, t) = \rho(T)c_p(T) \frac{\partial T(\vec{x}, t)}{\partial t} + \nabla[\kappa(T)\nabla T(\vec{x}, t)] - \rho(T)c_p(T)v_s \nabla T(\vec{x}, t)$$

$Q(x, t)$  [W/cm<sup>3</sup>] = Heat source  
= Energy deposited, consumed or absorbed by unit of volume

$\rho(T)$  [g/cm<sup>3</sup>] = Mass density

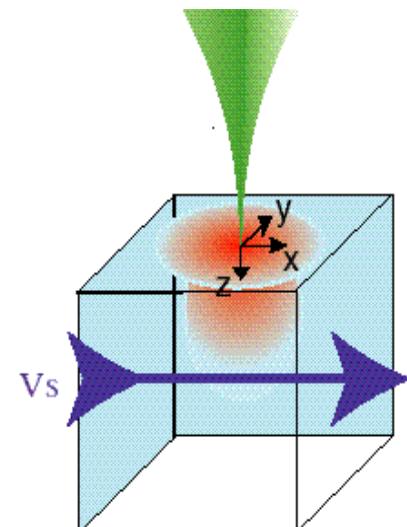
$c_p(T)$  [J/gK] = Specific heat at constant pressure

$v_s$  [cm/s] = Relative speed of sample to beam

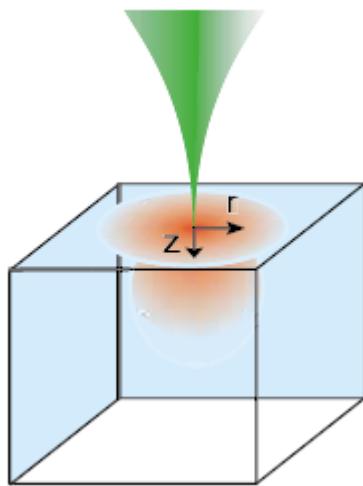
$\kappa$  [W/cm K] = Thermal conductivity

$D$  [cm<sup>2</sup>/s] = Heat diffusivity

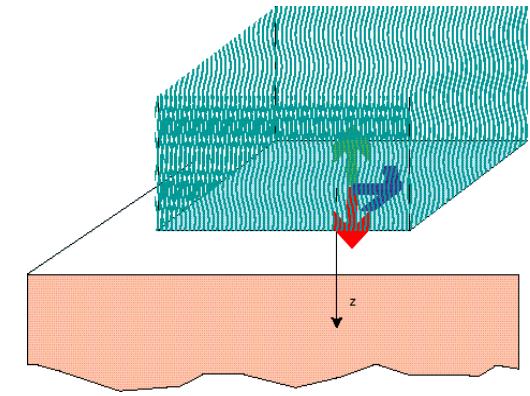
$$D = \frac{\kappa}{\rho c_p}$$



# Heat flow in 3 dimension



$$\frac{\partial T}{\partial t} = D \nabla^2 T + \frac{Q}{\rho c_p} \delta(\vec{x}, t)$$



Solution:

$$T(x, t) \approx \frac{Q}{\rho c_p (4\pi D t)^{m/2}} \exp\left(-\frac{|x|^2}{4Dt}\right)$$

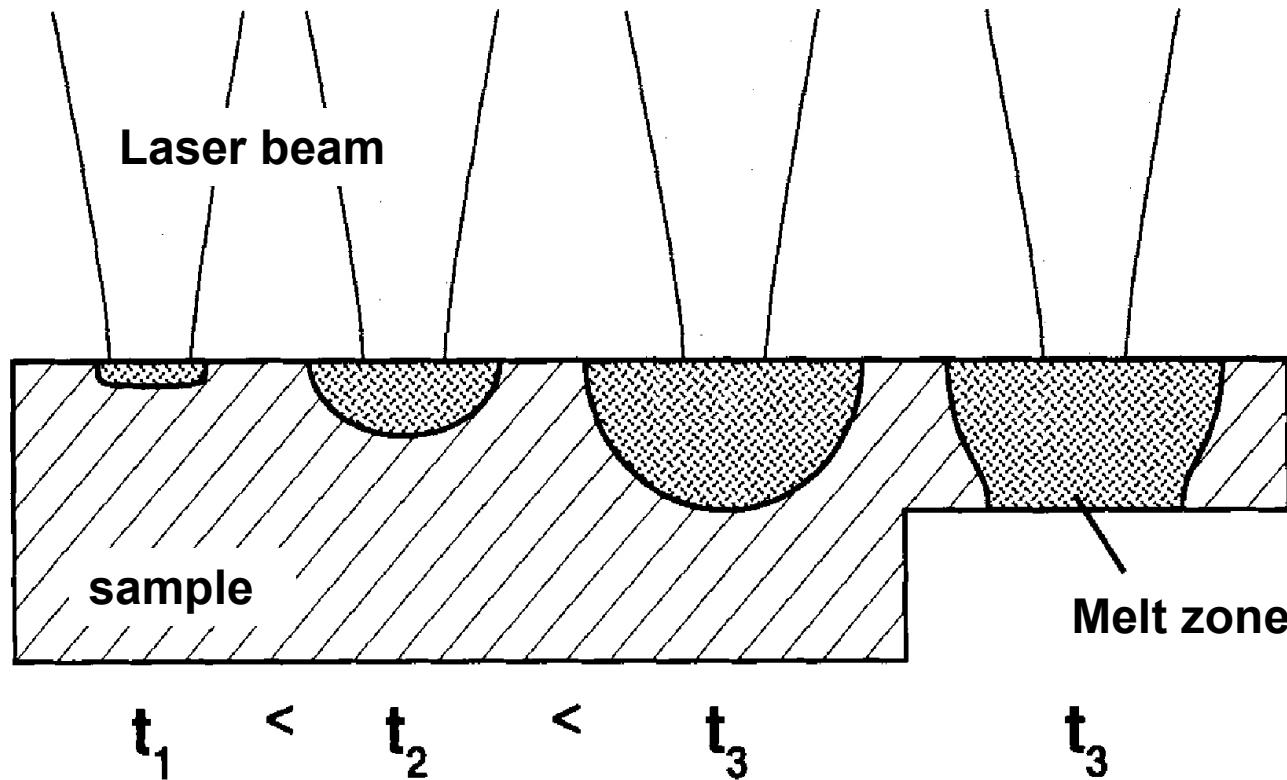
$m$  = dimension of problem ( $m = 1, 2, 3$ )

$Q$  = total energy deposited

$\rho$  = mass density per distance, surface or volume ( $\text{g/cm}^m$ )

# Laser Welding

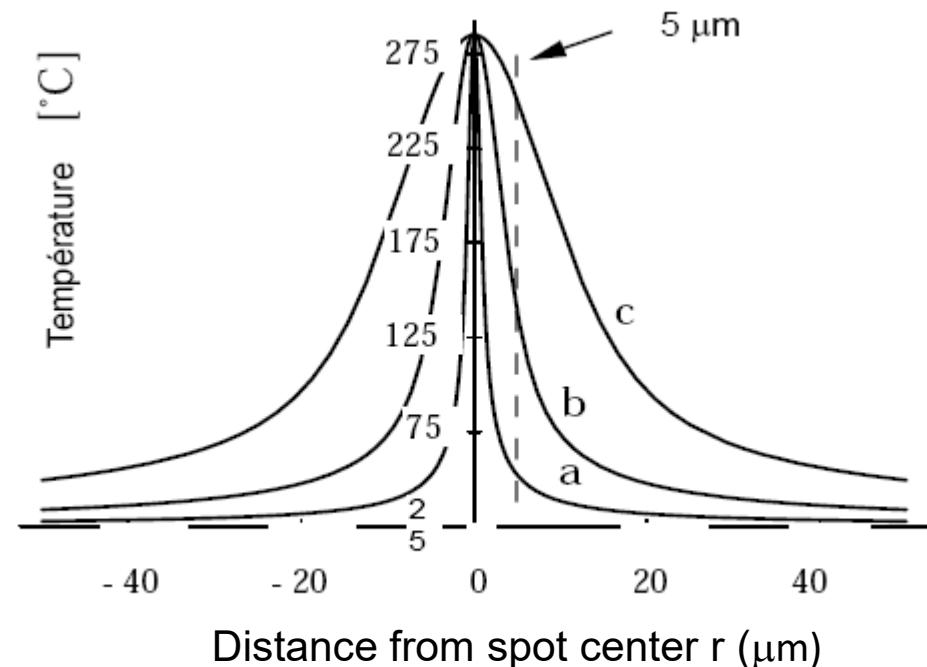
What is the dimensionality of the heat flow problem at each of the stages?



# Result of linearized heat equation

- Semi-infinite substrate

- Si,  $\lambda = 514 \text{ nm}$ 
  - All optimized to get  $T_{\max}$  in center of  $287^\circ\text{C}$

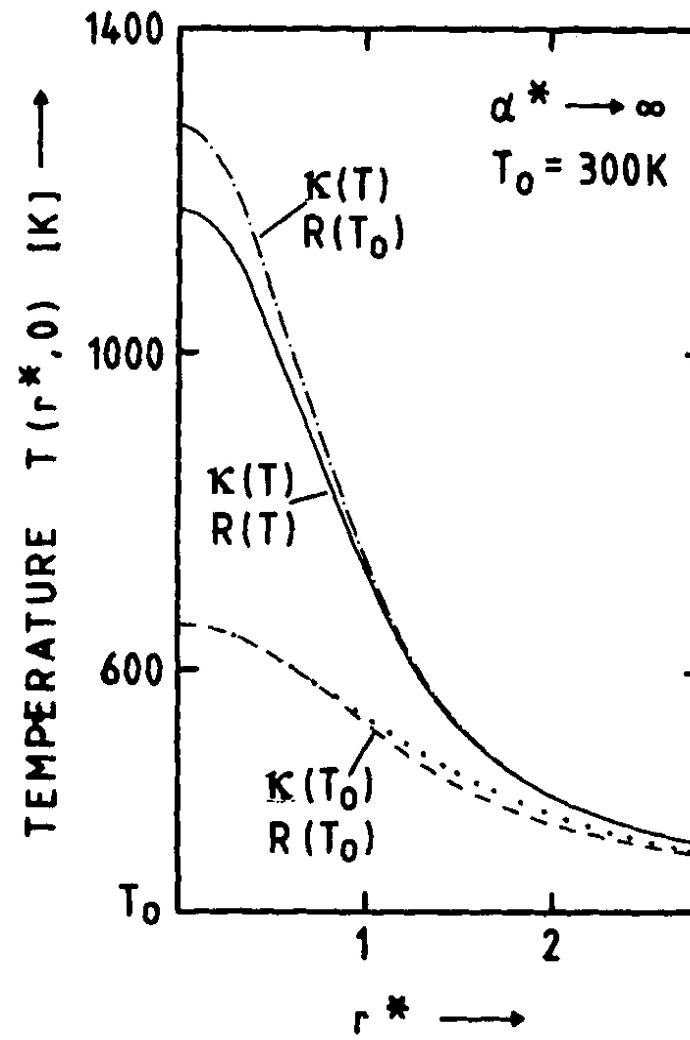


case	Waist $w_0$ (μm)	Power (mW)
a	1	173.5
b	5	574
c	15	1535

# Result of numerical heat flow simulations

- Semi-infinite substrate
- Si,  $\lambda = 514 \text{ nm}$

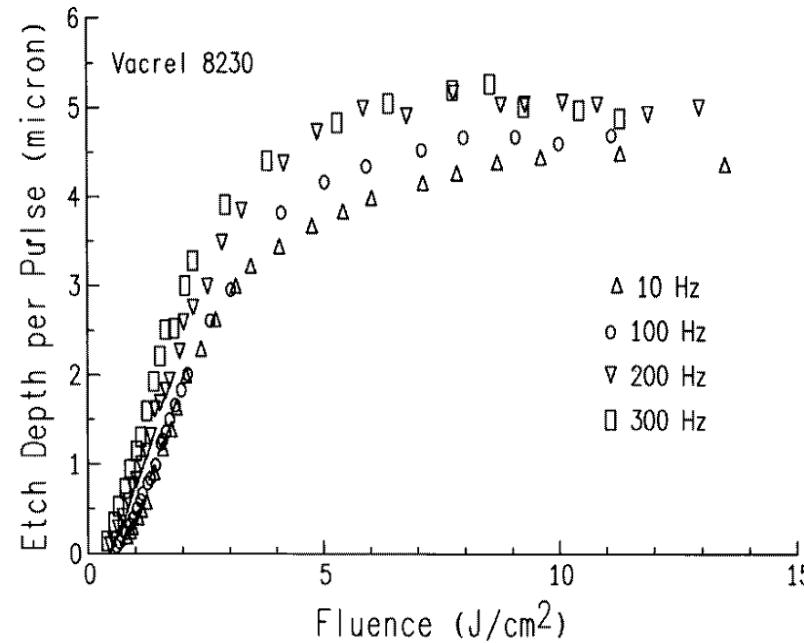
temperature dependence of heat conductivity and reflectivity is important to consider!!!!



# Heat Accumulation - Effect of the Repetition Rate

## Photoresist Vacre 8230

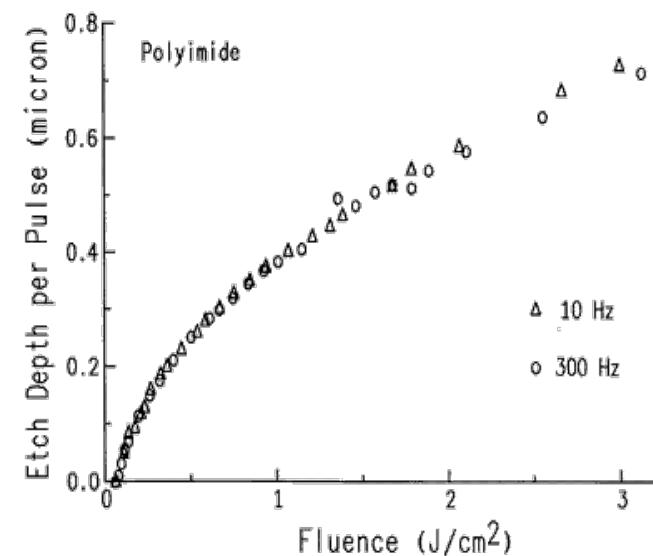
$\alpha \sim 5000 \text{ cm}^{-1}$  @ 308 nm – deep light penetration effect visible at low rep. rate



**Figure 3.** Ablation etching rate curves for Vacre<sup>TM</sup> 8230 photoresist measured at 308 nm and 10, 100, 200 and 300 Hz. There is a clear shift in the ablation etching rate curves to lower fluence as the repetition rate increases.

## Polyimide

$\alpha \sim 10^5 \text{ cm}^{-1}$  @ 308 nm - absorption on the surface Effect will be visible only at high rep. rate



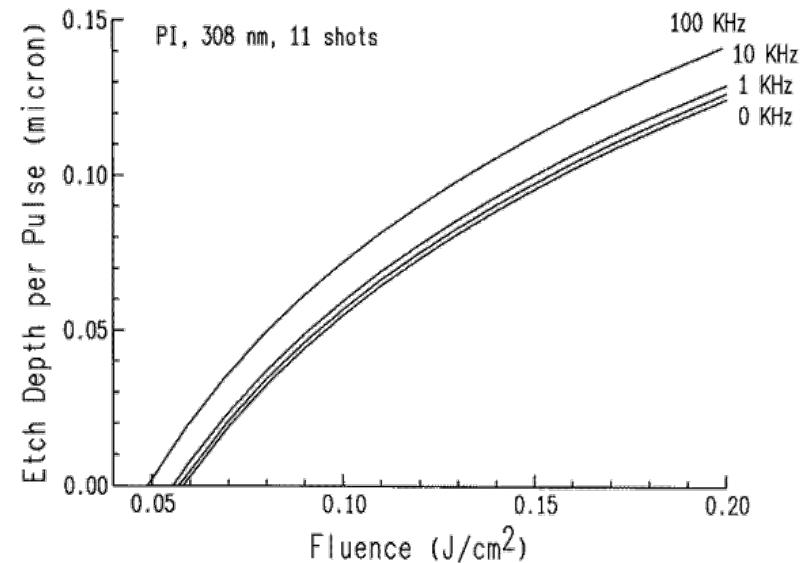
**Figure 2.** Ablation etching rates for polyimide measured at 308 nm and 10 and 300 Hz. There is no repetition rate effect for polyimide in this range of repetition rates.

# Heat Accumulation

Polyimide

$\alpha \sim 10^5 \text{ cm}^{-1}$  @ 308 nm - absorption on the surface

Effect will be visible only at high rep.rate



**Figure 6.** The simulated etching rate versus fluence for PI at 308 nm. Curves for repetition rates of 0, 1 and 10 kHz are closely grouped.

high repetition rate  $\nu$  results in heat accumulation effect and increase in ablation rate

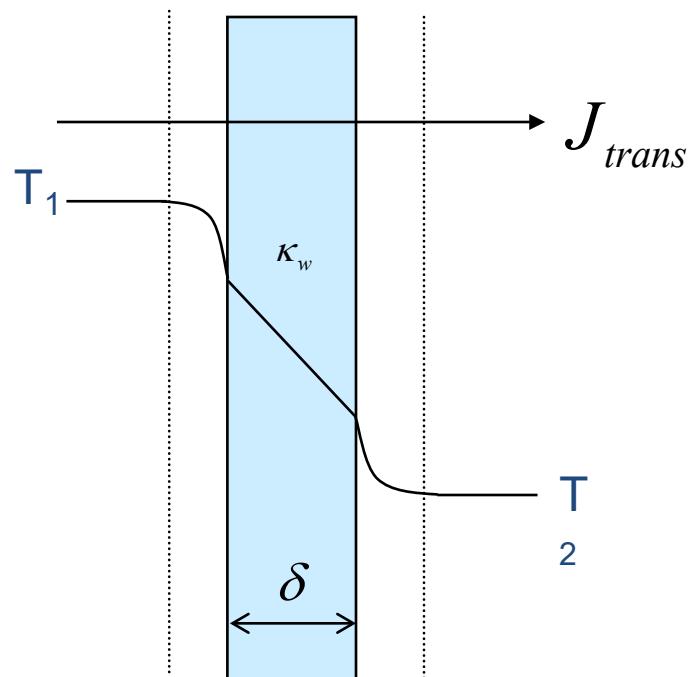
$$\nu \approx 0.1 D \alpha_{eff}^2 / N$$

Burns F.C. and Cain S.R.;  
J. Phys. D. Appl. Phys., 29 (1996)  
1349

# Complete heat transfert through wall/window

$$J_{trans} = A(T_1 - T_2) \eta_{trans}$$

$$J_{trans} : [J / s = W]$$



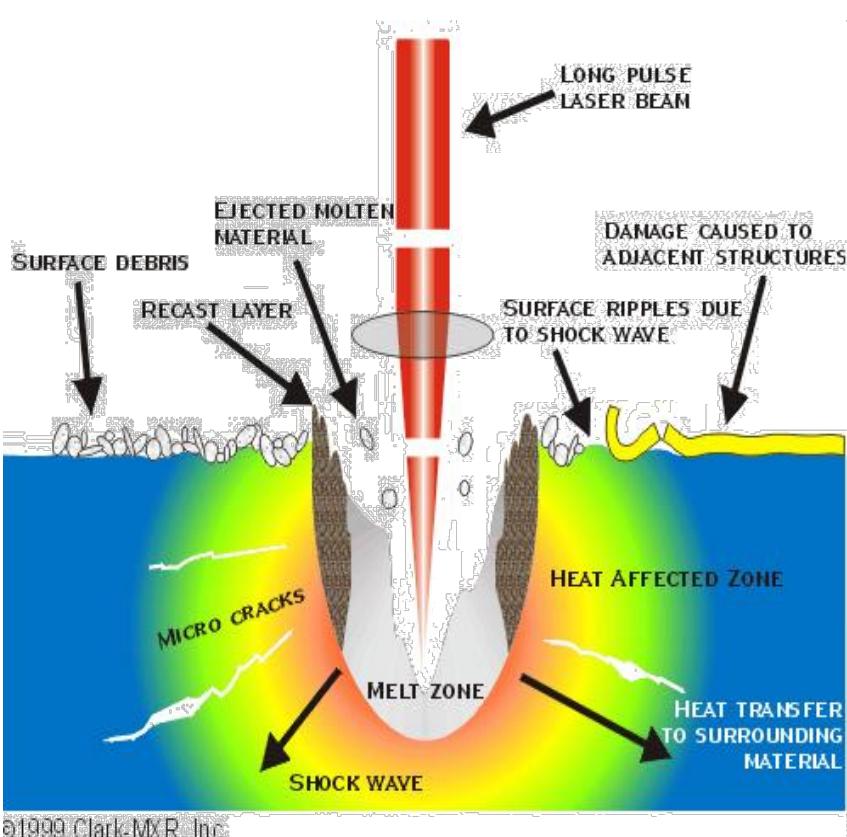
$$\eta_{trans} = \frac{1}{\frac{1}{\eta_1} + \frac{\delta}{\kappa_w} + \frac{1}{\eta_2}} \left[ \frac{J}{cm^2 s K} \right]$$

window  $\eta_{trans} = 2 \cdot 10^{-4} [W / cm^2 K]$

wall  $\eta_{trans} = 0.5 \cdot 10^{-4} [W / cm^2 K]$



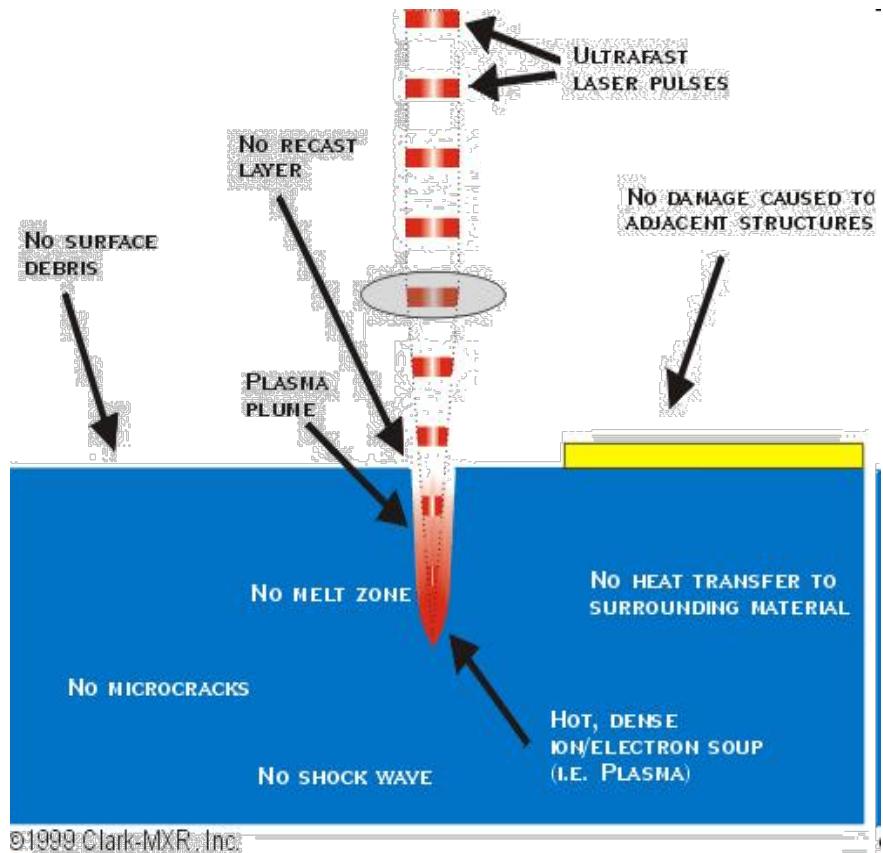
# ns-machining vs. fs-machining



©1999 Clark-MXR, Inc.



ns



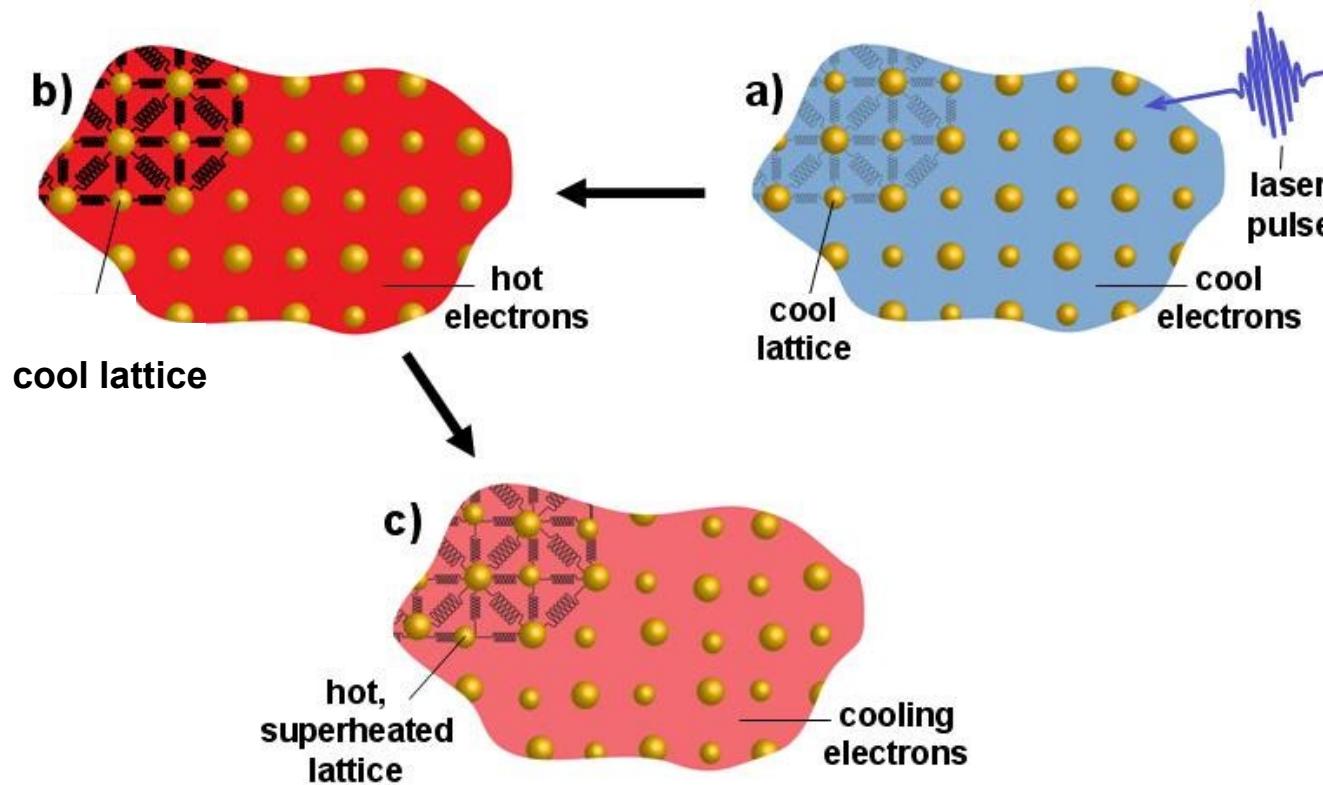
©1999 Clark-MXR, Inc.



fs

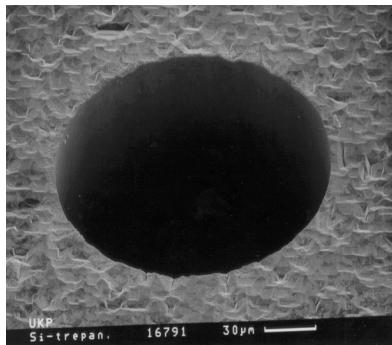
# Ultrafast Laser Pulses

for  $\tau < 1-10$  ps pulses - light absorption is faster than heat transfer from electron to atoms

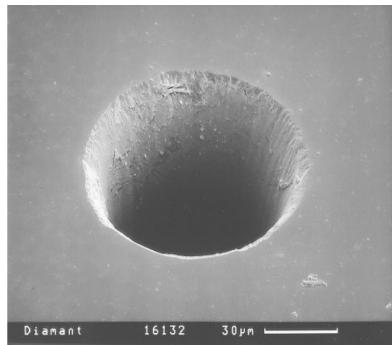


heating rate is very high – heat penetration is low  $l_{th} \approx 2(D\tau_l)^{1/2}$

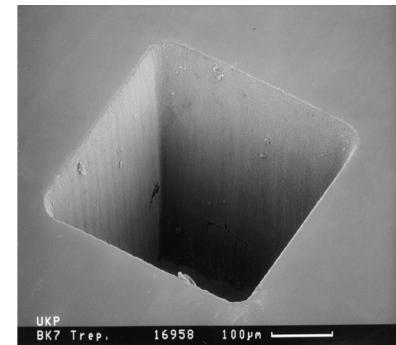
# fs-laser machining



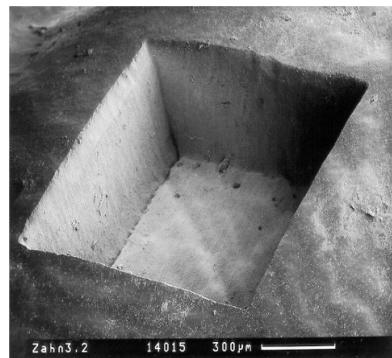
Silizium



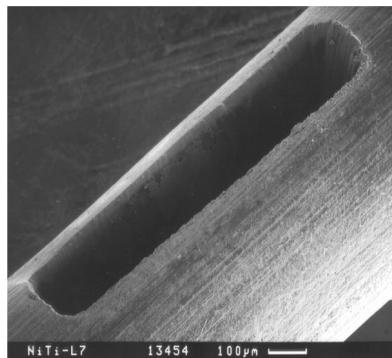
Diamant



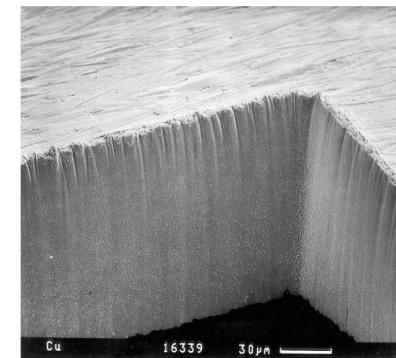
Glas



Zahnschmelz



Speziallegierungen



Kupfer



LASER ZENTRUM HANNOVER E.V.